

### **N-channel SiC power MOSFET**

$V_{\mathrm{DSS}}$	650V
R <sub>DS(on)</sub> (Typ.)	120m $Ω$
I <sub>D</sub>	21A
$P_D$	103W

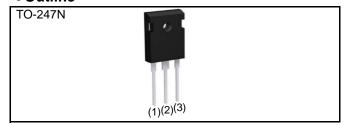
#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

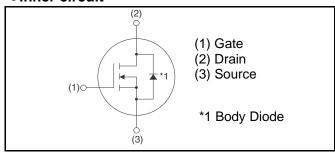
### Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

#### Outline



#### ●Inner circuit



Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3120AL

#### ◆Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{ extsf{DSS}}$	650	V	
Continuous drain current	T <sub>c</sub> = 25°C	I <sub>D</sub> *1	21	А
Continuous drain current	T <sub>c</sub> = 100°C	l <sub>D</sub> *1	15	А
Pulsed drain current	I <sub>D,pulse</sub> *2	52	А	
Gate - Source voltage		$V_{GSS}$	-4 to 22	V
Gate-Source Surge Voltage	$V_{GSS\_surge}$	−4 to 22	V	
Recommended Drive Voltage		$V_{GS\_op}$	0 / 18	V
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +175	°C	

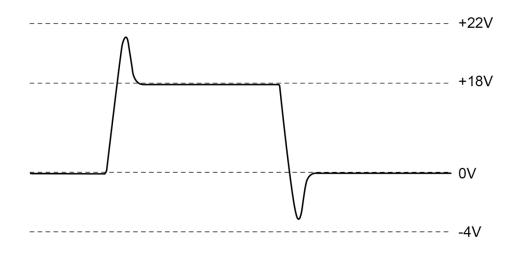
#### ●Thermal resistance

Parameter	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	
Thermal resistance, junction - case	R <sub>thJC</sub>	-	1.12	1.46	°C/W

# •Electrical characteristics $(T_a = 25^{\circ}C)$

Doromotor	Cymhol	Conditions	Values			Unit
Parameter	Symbol	mbol Conditions -		Тур.	Max.	Onit
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	650	-	-	V
		$V_{DS} = 650 \text{V}, V_{GS} = 0 \text{V}$				
Zero gate voltage drain current	I <sub>DSS</sub>	$T_j = 25^{\circ}C$	-	1	10	μΑ
		T <sub>j</sub> = 150°C	-	2	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS</sub> _	$V_{GS} = -4V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = 10V, I_{D} = 3.33 \text{mA}$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 6.7A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *3	T <sub>j</sub> = 25°C	-	120	156	mΩ
		T <sub>j</sub> = 125°C	-	158.4	-	
Gate input resistance	R <sub>G</sub>	f = 1MHz, open drain	-	18	-	Ω

### ●Example of acceptable Vgs waveform



## ●Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Cumbal	Symbol Conditions -		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	<b>g</b> fs *3	$V_{DS} = 10V, I_D = 6.7A$	-	2.7	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	460	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 500V	-	35	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	16	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 300V	-	70	•	pF
Turn - on delay time	t <sub>d(on)</sub> *3	$V_{DD} = 300V, I_D = 6.7A$	-	14	-	
Rise time	t <sub>r</sub> *3	V <sub>GS</sub> = 18V/0V	-	21	-	20
Turn - off delay time	t <sub>d(off)</sub> *3	$R_L = 45\Omega$	-	23	-	ns
Fall time	t <sub>f</sub> *3	$R_G = 0\Omega$	-	14	-	
Turn - on switching loss	E <sub>on</sub> *3	$V_{DD} = 300V, I_{D} = 6.7A$ $V_{GS} = 18V/0V$	-	29	-	1
Turn - off switching loss	E <sub>off</sub> *3	R <sub>G</sub> = 0Ω L=500μH *E <sub>on</sub> includes diode reverse recovery	-	3	-	μJ

## •Gate Charge characteristics ( $T_a = 25$ °C)

Parameter	Symbol Co	Conditions	Values			Unit
raiametei		Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*3}$	V <sub>DD</sub> = 300V	-	38	-	
Gate - Source charge	Q <sub>gs</sub> *3	$I_{D} = 6.7A$	-	11	-	nC
Gate - Drain charge	Q <sub>gd</sub> *3	V <sub>GS</sub> = 18V	-	13	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 300V, I_D = 6.7A$	-	9.6	1	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

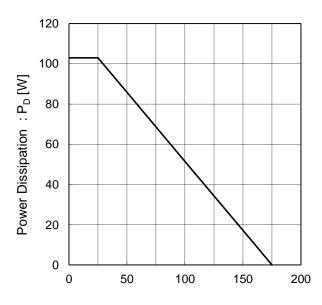
<sup>\*2</sup> PW  $\leq$  10  $\mu s,$  Duty cycle  $\leq$  1%

<sup>\*3</sup> Pulsed

## ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

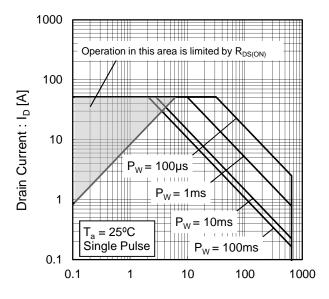
Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Symbol Conditions		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	-T <sub>c</sub> = 25°C	-	1	21	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		-	-	52	А
Forward voltage	V <sub>SD</sub> *3	$V_{GS} = 0V, I_{S} = 6.7A$	-	3.2	ı	V
Reverse recovery time	t <sub>rr</sub> *3		-	13	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *3	I <sub>F</sub> = 6.7A, V <sub>R</sub> = 300V di/dt = 1100A/μs	-	35	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *3		-	6	-	Α

Fig.1 Power Dissipation Derating Curve

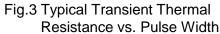


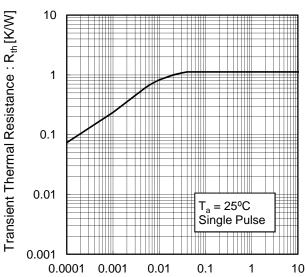
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



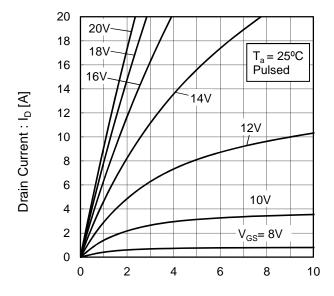
Drain - Source Voltage :  $V_{DS}$  [V]





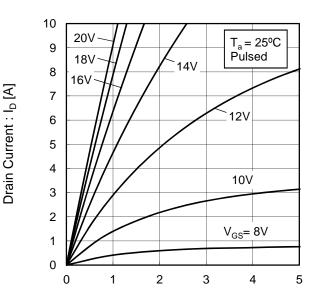
Pulse Width: P<sub>W</sub> [s]

Fig.4 Typical Output Characteristics(I)

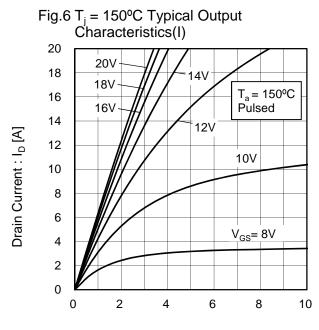


Drain - Source Voltage : V<sub>DS</sub> [V]

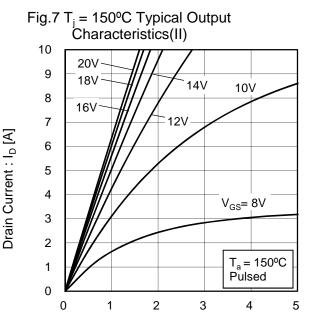
Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]



Drain - Source Voltage :  $V_{DS}[V]$ 



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.8 Typical Transfer Characteristics (I)

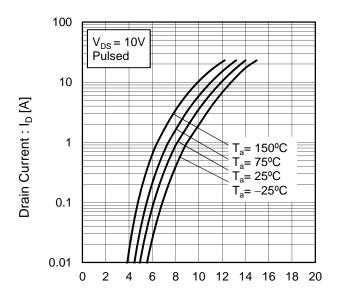
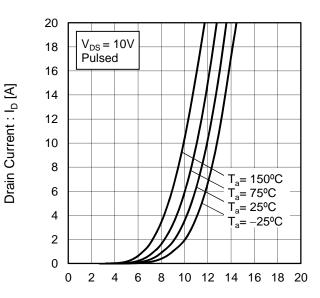


Fig.9 Typical Transfer Characteristics (II)

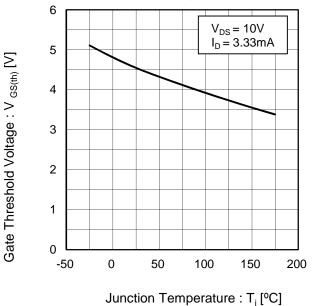


Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.11 Transconductance vs. Drain Current

Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Transconductance : g<sub>fs</sub> [S]

10  $V_{DS} = 10V$ Pulsed  $T_a = 150^{\circ}C$  $T_a = 75^{\circ}C$  $T_a = 25^{\circ}C$  $T_a = -25^{\circ}C$ 0.1 0.1 1 10

Drain Current : I<sub>D</sub> [A]

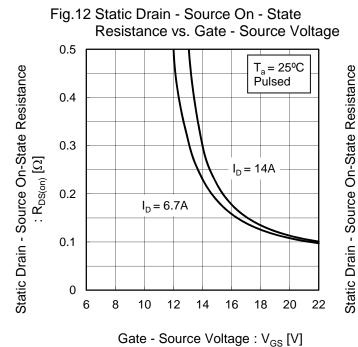
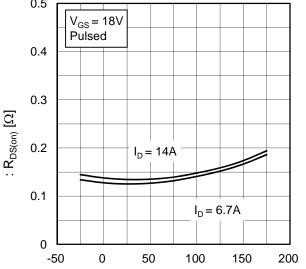
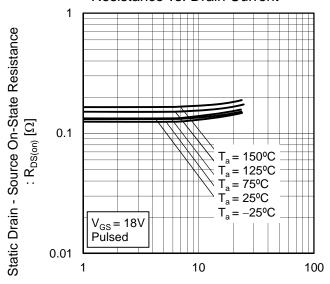


Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current: I<sub>D</sub> [A]

10

1

0.1

#### •Electrical characteristic curves

 $T_a = 25^{\circ}C$ 

f = 1MHz  $V_{GS} = 0V$ 

Fig.15 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Capacitance: C [pF]  $C_{oss}$ 100 

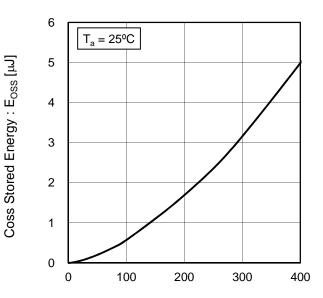
Drain - Source Voltage : V<sub>DS</sub> [V]

100

1000

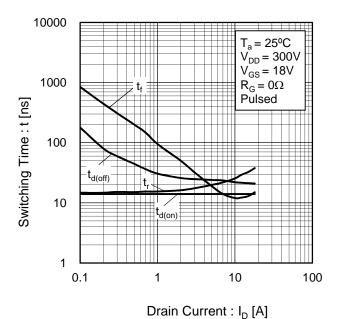
10

Fig.16 Coss Stored Energy



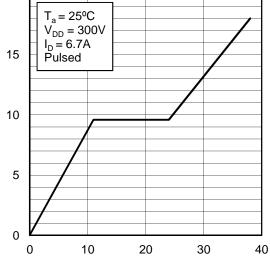
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.17 Switching Characteristics



20  $T_a = 25^{\circ}C$ 

Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>g</sub> [nC]

3ate - Source Voltage: V<sub>GS</sub> [V]

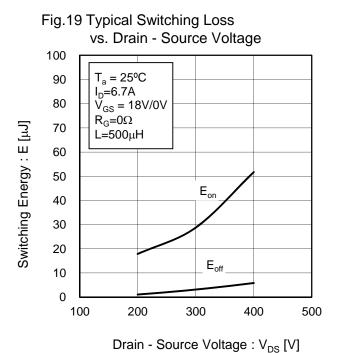
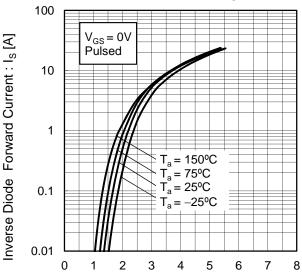


Fig.20 Typical Switching Loss vs. Drain Current 200  $T_a = 25^{\circ}C$  $V_{DD} = 300V$  $V_{GS} = 18V/0V$  $R_{G} = 0\Omega$ Switching Energy : E [µJ] 150 L=500uH 100  $\mathsf{E}_{\mathsf{on}}$ 50  $\mathsf{E}_{\mathsf{off}}$ 0 0 5 10 15 20 Drain Current: I<sub>D</sub> [A]

Fig.21 Typical Switching Loss vs. External Gate Resistance 200  $T_a = 25^{\circ}C$ V<sub>DD</sub>=300V  $I_{D} = 6.7A$   $V_{GS} = 18V/0V$   $L = 500 \mu H$ 150 Switching Energy: E [μJ] 100  $\mathsf{E}_{\mathsf{on}}$ 50  $\mathsf{E}_{\mathsf{off}}$ 0 5 0 10 15 20 25 30

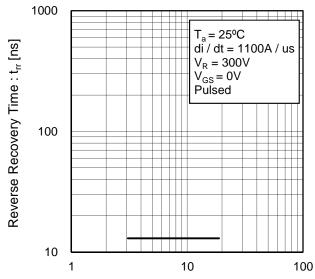
External Gate Resistance :  $R_G[\Omega]$ 

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

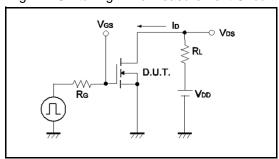


Fig.2-1 Gate Charge Measurement Circuit

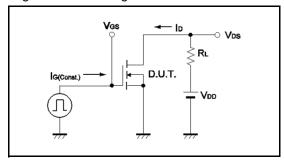


Fig.3-1 Switching Energy Measurement Circuit

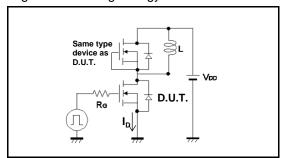


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

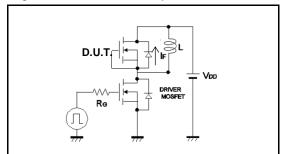


Fig.1-2 Switching Waveforms

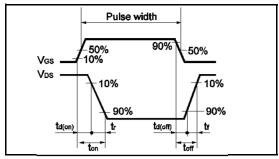


Fig.2-2 Gate Charge Waveform

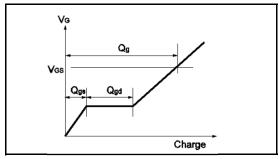
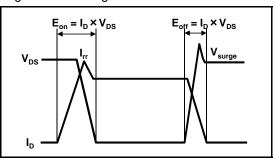
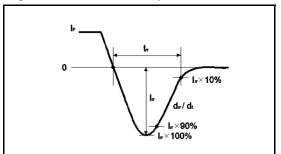


Fig.3-2 Switching Waveforms





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# SCT3120AL - Web Page

**Distribution Inventory** 

Part Number	SCT3120AL
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes